Metal-Free, Single-Polymer Device Exhibits Resistive Memory Effect

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SUPPLEMENTARY INFORMATION

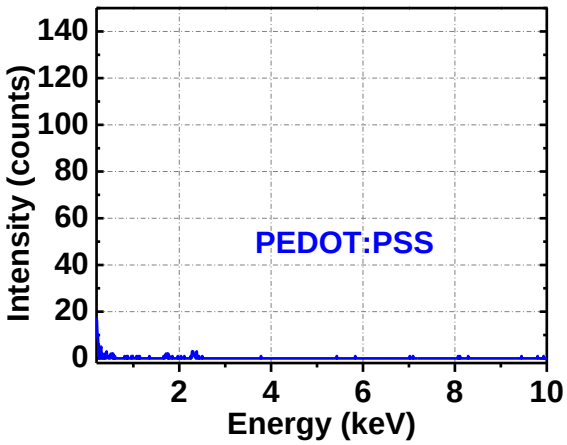

Figure S1. EDX spectrum of PEDOT: PSS active layer adjacent to the gold filament

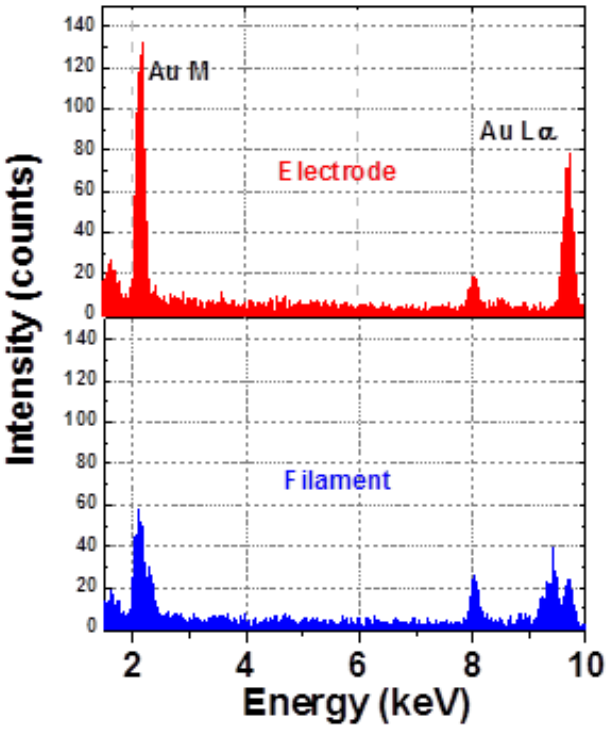

Figure S2. EDX spectrum of Au electrode and Au filament

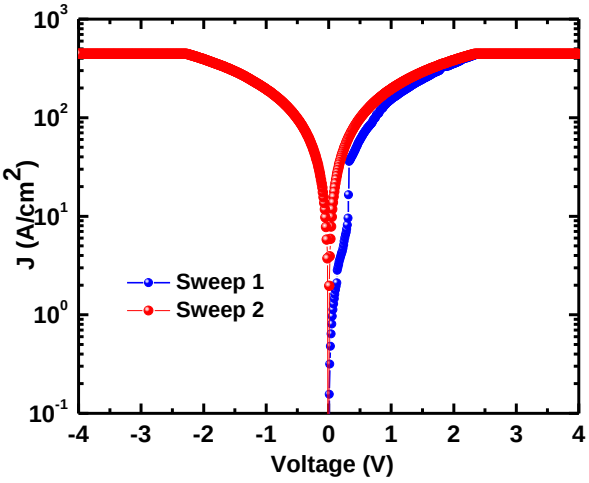

Figure S3. I-V characteristics of PEDOT:PSS memory devices with Pt-Au electrodes upto 4 V

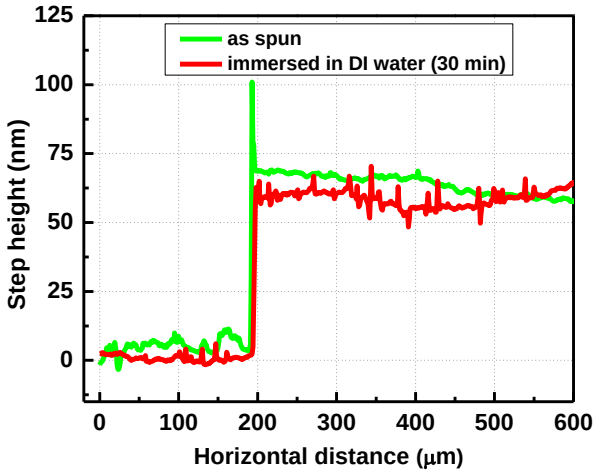

Figure S4. Profilometer thickness of PEDOT:PSS thin films as spun and after immersing in DI water

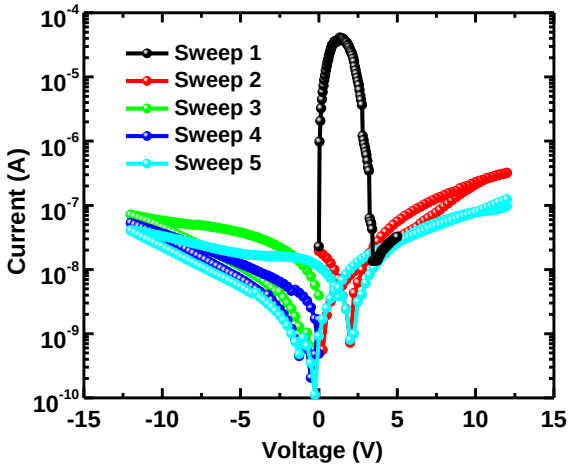

Figure S5. I-V characteristics of all PEDOT:PSS WORM memory devices upto 12 V